



浙江芯芯电子有限公司
ZHEJIANG XINXIN ELECTIRICAL CO., LTD.

产品规格书

Specification of Products

产品名称：可控硅模块

产品型号：MTG50A

浙江芯芯电子有限公司

ZHEJIANG XINXIN ELECTIRICAL CO., LTD.

地址：浙江省缙云县壶镇镇浙江丽缙五金科技产业园苍山区块内

电话：13857067071

邮编：321404

E-mail:247145749@qq.com

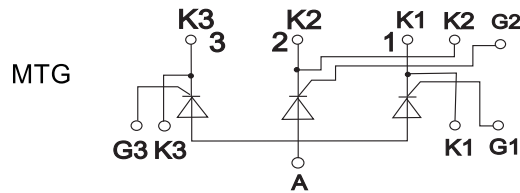
<http://www.zjxxdz1.com>

拟制	审核	核准
丁国盛	李园利	麻伟阳

版本号：04 更新日期：2022.6.28

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{T(AV)}	Mean on-state current	180° half sine wave 50Hz Single side cooled, T _C =90° C	125			50	A
I _{T(RMS)}	RMS on-state current	Single side cooled, T _C =90° C	125			79	A
V _{DRM} V _{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V _{DRM} &V _{RRM} tp=10ms V _{DSM} &V _{RSM} = V _{DRM} &V _{RRM} +200V respectively	125	800		1800	V
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}	125			8	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			1.60	KA
I ² t	I ² T for fusing coordination	V _R =60%V _{RRM}				13.0	A ² s*10 ³
V _{TO}	Threshold voltage		125			0.80	V
r _T	On-state slop resistance					5.41	mΩ
V _{TM}	Peak on-state voltage	I _{TM} =150A	125			1.4	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =67%V _{DRM}	125			800	V/μs
di/dt	Critical rate of rise of on-state current	From 67%V _{DRM} to 150A, Gate source 1.5A t _r ≤0.5μs Repetitive	125			100	A/μs
I _{GT}	Gate trigger current	V _A =12V, I _A =1A	25	30		100	mA
V _{GT}	Gate trigger voltage			0.8		2.0	V
I _H	Holding current			20		100	mA
V _{GD}	Non-trigger gate voltage	At 67%V _{DRM}	125			0.2	V
R _{th(j-c)}	Thermal resistance Junction to heatsink	Single side cooled				0.480	°C /W
F _m	Thermal connection torque(M5)				2.0		N.m
	Mounting torque(M6)				3.0		N.m
T _{stg}	Stored temperature			-40		140	° C
W _t	Weight				150		g
Outline							

OUTLINE DRAWING & CIRCUIT DIAGRAM



Rating and Characteristic

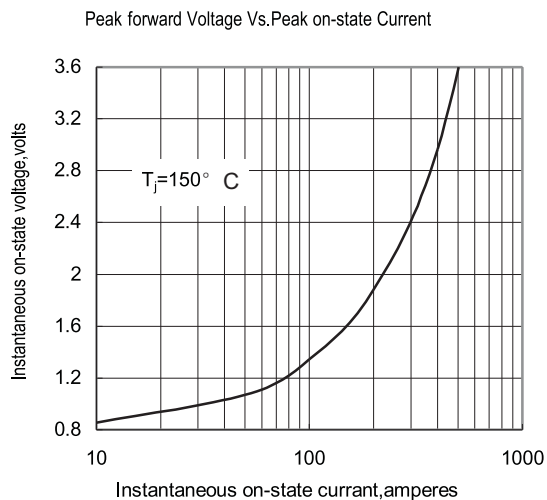


Fig.1

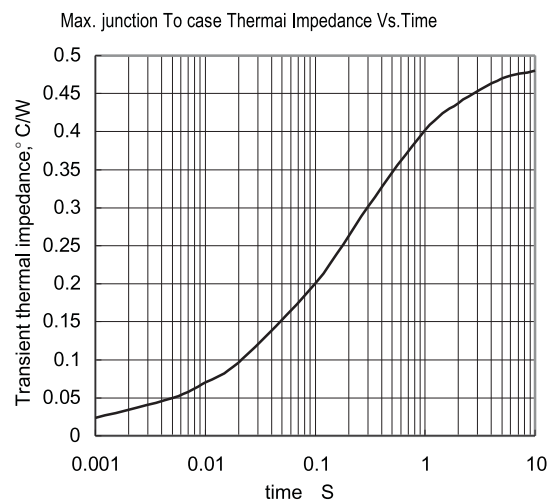


Fig.2

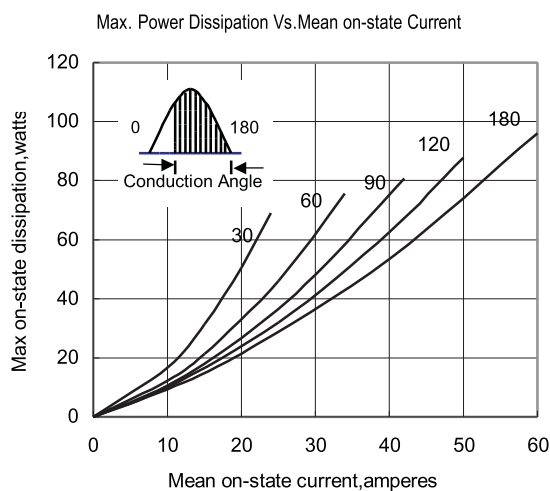


Fig.3

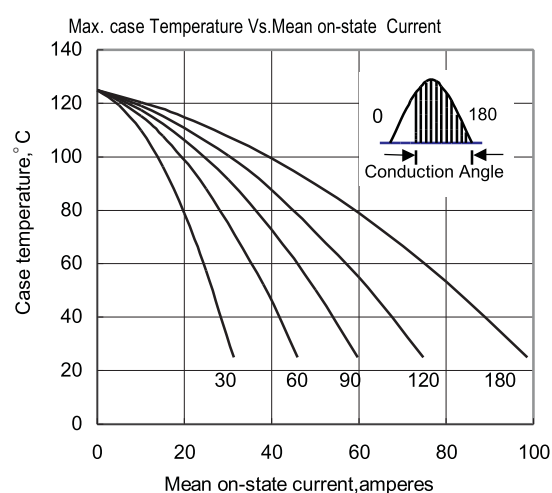


Fig.4

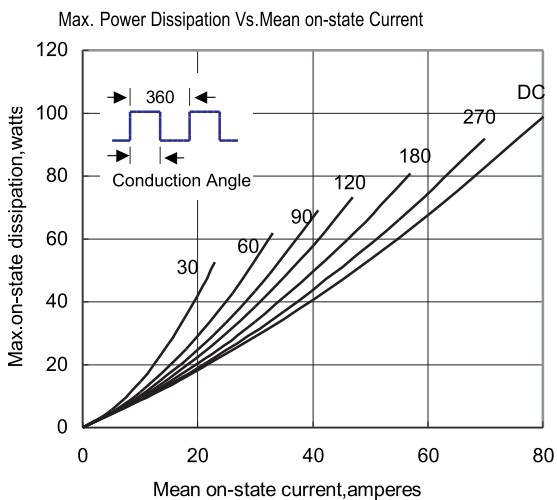


Fig.5

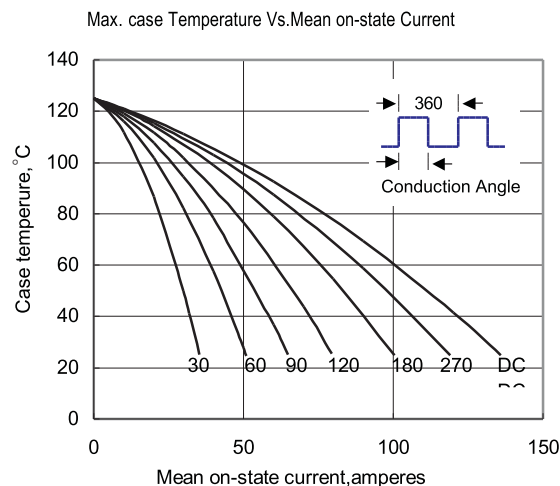


Fig.6

Outside Dimension

